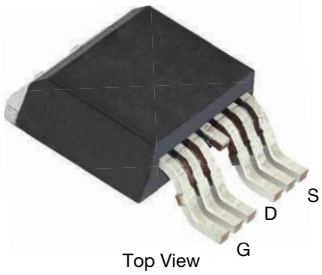
Automotive N-Channel 40 V (D-S) 175 °C MOSFET

TO-263 7-Lead



Top View

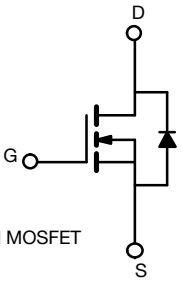
FEATURES

- TrenchFET® power MOSFET
- Package with low thermal resistance
- 100 % R_g and UIS tested
- AEC-Q101 qualified
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

AUTOMOTIVE GRADE

RoHS COMPLIANT

HALOGEN FREE



N-Channel MOSFET

PRODUCT SUMMARY	
V_{DS} (V)	40
$R_{DS(on)}$ (Ω) at V_{GS} = 10 V	0.00100
I_D (A)	200
Configuration	Single
Package	TO-263-7L

ABSOLUTE MAXIMUM RATINGS (T_C = 25 °C, unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNIT
Drain-source voltage		V_{DS}	40	V
Gate-source voltage		V_{GS}	± 20	
Continuous drain current [a]	T_C = 25 °C	I_D	200	A
	T_C = 125 °C		200	
Continuous source current (diode conduction) [a]		I_S	200	
Pulsed drain current [b]		I_{DM}	260	
Single pulse avalanche current	L = 0.1 mH	I_{AS}	100	
Single pulse avalanche energy		E_{AS}	500	mJ
Maximum power dissipation [b]	T_C = 25 °C	P_D	375	W
	T_C = 125 °C		125	
Operating junction and storage temperature range		T_J, T_{stg}	-55 to +175	°C

THERMAL RESISTANCE RATINGS

PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-ambient	PCB mount [c]	R_{thJA}	40	°C/W
Junction-to-case (drain)		R_{thJC}	0.4	

Notes

a. Package limited
b. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %
c. When mounted on 1" square PCB (FR4 material)

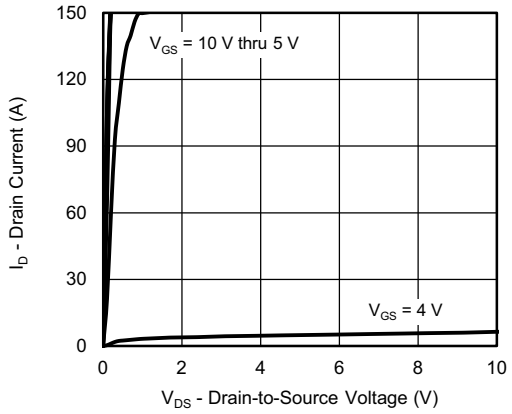
SPECIFICATIONS (T_C = 25 °C, unless otherwise noted)							
PARAMETER	**SYMBOL**	**TEST CONDITIONS**		**MIN.**	**TYP.**	**MAX.**	**UNIT**
Static							
Drain-source breakdown voltage	V_{DS}	V_{GS} = 0 V, I_D = 250 µA		40	-	-	V
Gate-source threshold voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250 µA		2.5	3.0	3.5	
Gate-source leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ± 20 V		-	-	± 100	nA
Zero gate voltage drain current	I_{DSS}	V_{GS} = 0 V	V_{DS} = 40 V	-	-	1	µA
		V_{GS} = 0 V	V_{DS} = 40 V, T_J = 125 °C	-	-	50	
		V_{GS} = 0 V	V_{DS} = 40 V, T_J = 175 °C	-	-	300	µA
On-state drain current [a]	$I_{D(on)}$	V_{GS} = 10 V	V_{DS} ≥ 5 V	100	-	-	A
Drain-source on-state resistance [a]	$R_{DS(on)}$	V_{GS} = 10 V	I_D = 35 A	-	0.00084	0.00100	Ω
		V_{GS} = 10 V	I_D = 35 A, T_J = 125 °C	-	-	0.00140	
		V_{GS} = 10 V	I_D = 35 A, T_J = 175 °C	-	-	0.00164	
Forward transconductance [b]	g_{fs}	V_{DS} = 15 V, I_D = 30 A		-	196	-	S
Dynamic [b]							
Input capacitance	C_{iss}	V_{GS} = 0 V	V_{DS} = 25 V, f = 1 MHz	-	11 938	15 525	pF
Output capacitance	C_{oss}			-	11 163	14 520	
Reverse transfer capacitance	C_{rss}			-	282	370	
Total gate charge [c]	Q_g	V_{GS} = 10 V	V_{DS} = 20 V, I_D = 100 A	-	158	250	nC
Gate-source charge [c]	Q_{gs}			-	44	-	
Gate-drain charge [c]	Q_{gd}			-	22	-	
Gate resistance	R_g	f = 1 MHz		2.70	5.44	8.20	Ω
Turn-on delay time [c]	$t_{d(on)}$	V_{DD} = 20 V, R_L = 0.2 Ω I_D ≅ 100 A, V_{GEN} = 10 V, R_g = 1 Ω		-	16	25	ns
Rise time [c]	t_r			-	10	17	
Turn-off delay time [c]	$t_{d(off)}$			-	103	160	
Fall time [c]	t_f			-	61	95	
Source-Drain Diode Ratings and Characteristics [b]							
Pulsed current [a]	I_{SM}			-	-	260	A
Forward voltage	V_{SD}	I_F = 60 A, V_{GS} = 0 V		-	0.81	1.5	V
Body diode reverse recovery time	t_{rr}	I_F = 30 A, di/dt = 100 A/µs		-	165	350	ns
Body diode reverse recovery charge	Q_{rr}			-	530	1100	nC
Reverse recovery fall time	t_a			-	66	-	ns
Reverse recovery rise time	t_b			-	99	-	
Body diode peak reverse recovery current	$I_{RM(REC)}$			-	-6.2	-	A

Notes

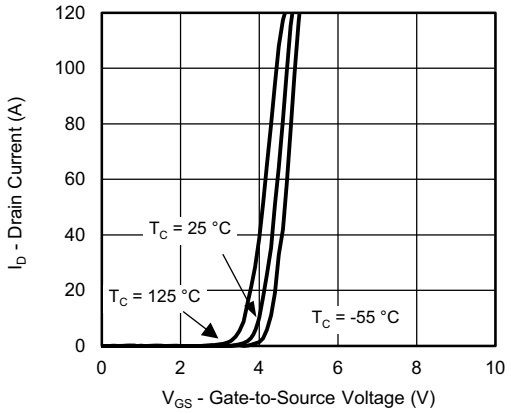
a. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %
b. Guaranteed by design, not subject to production testing
c. Independent of operating temperature

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

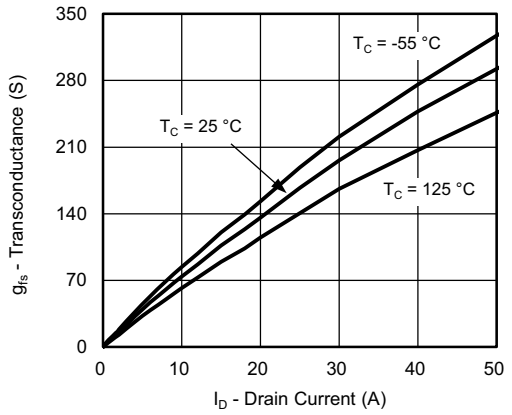
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



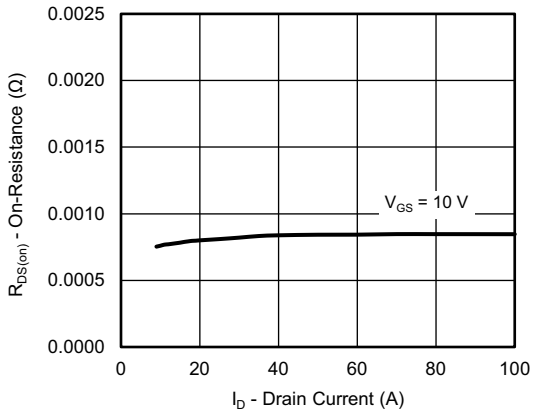
Output Characteristics



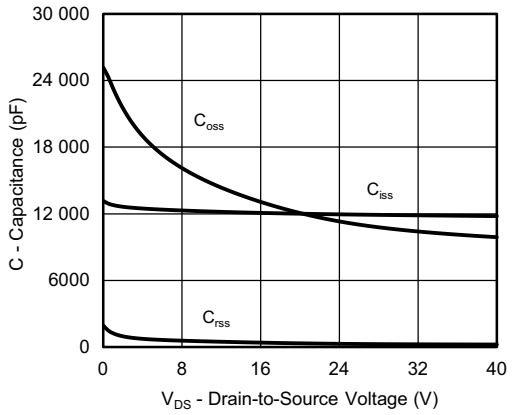
Transfer Characteristics



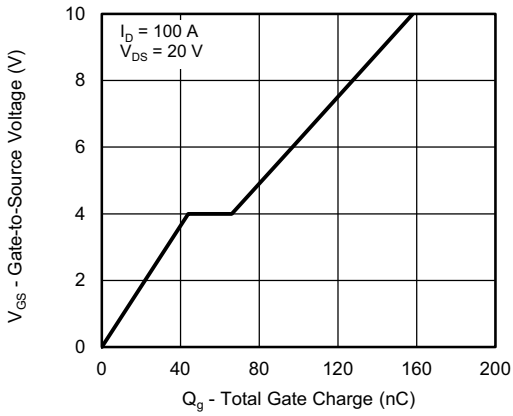
Transconductance



On-Resistance vs. Drain Current

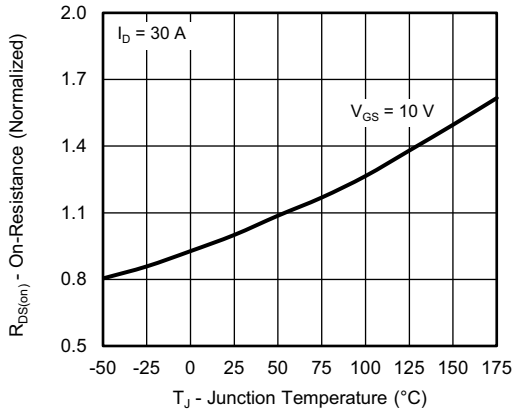


Capacitance

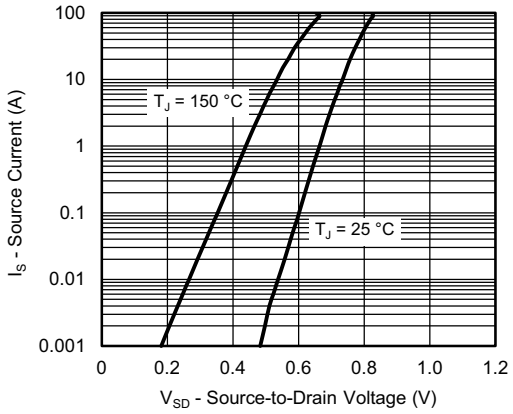


Gate Charge

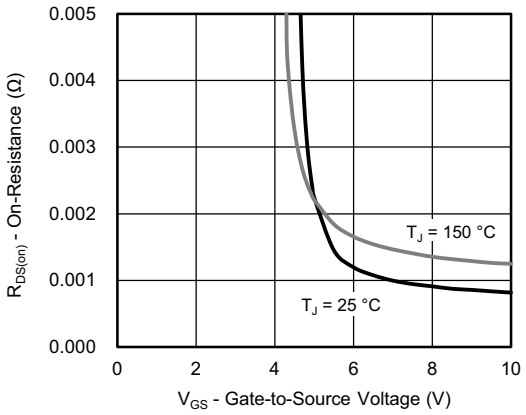
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



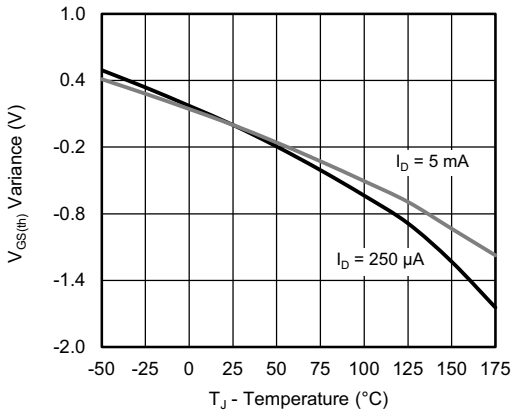
On-Resistance vs. Junction Temperature



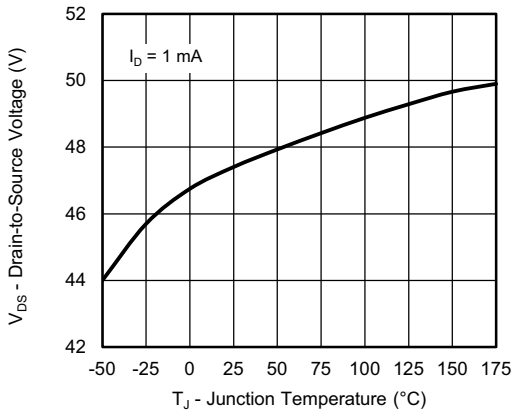
Source Drain Diode Forward Voltage



On-Resistance vs. Gate-to-Source Voltage

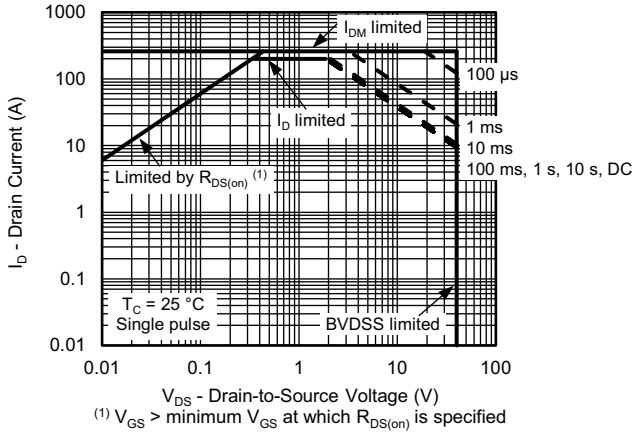


Threshold Voltage

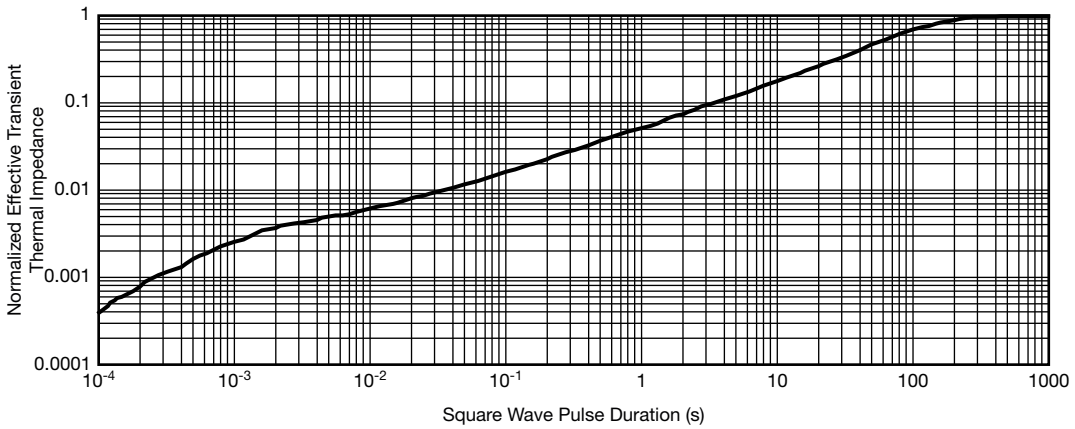


Drain Source Breakdown vs. Junction Temperature

THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)

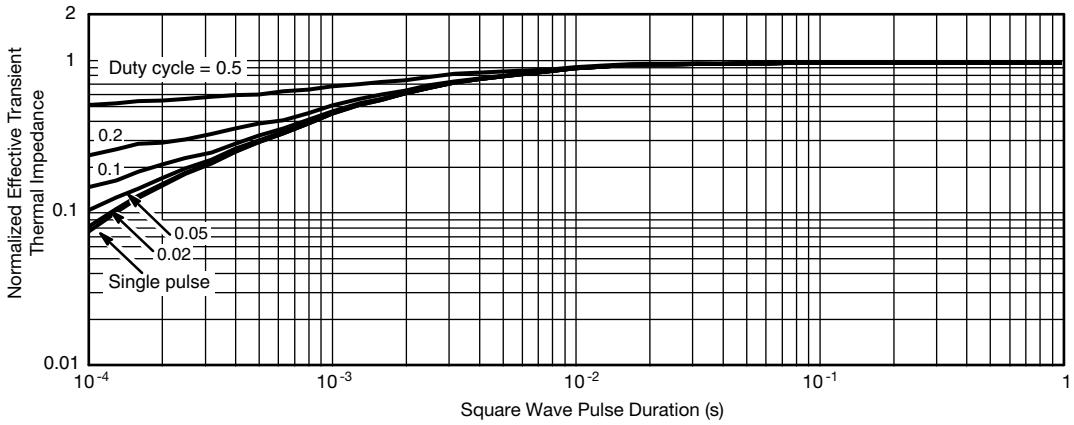


Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient

THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



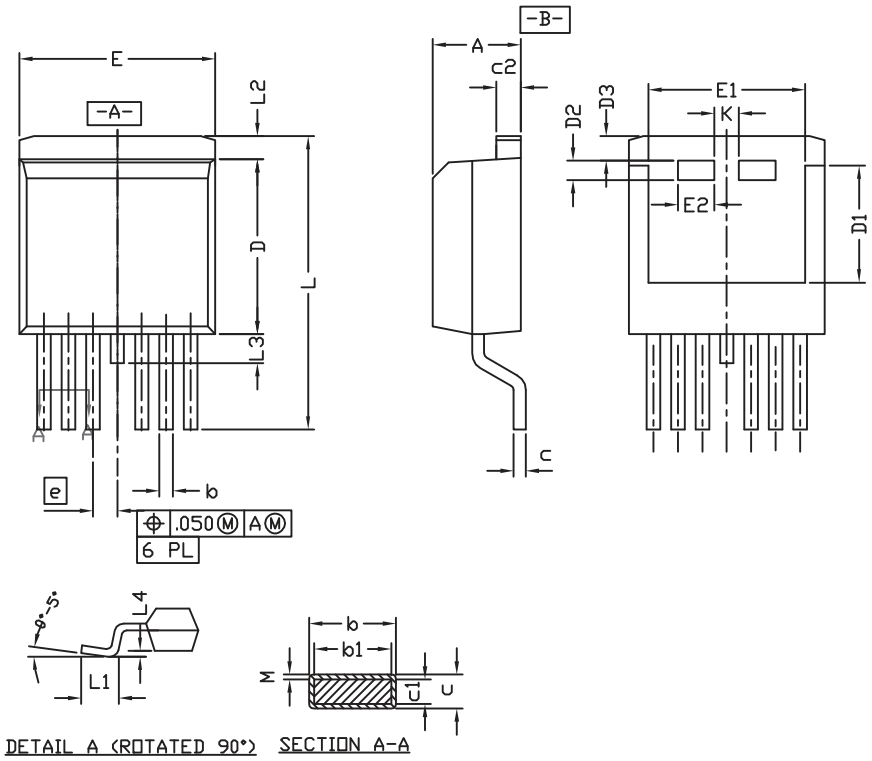
Normalized Thermal Transient Impedance, Junction-to-Case

Note

- The characteristics shown in the two graphs
  - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
  - Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

  are given for general guidelines only to enable the user to get a “ball park” indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions

D²PAK (TO-263-7L) Case Outline

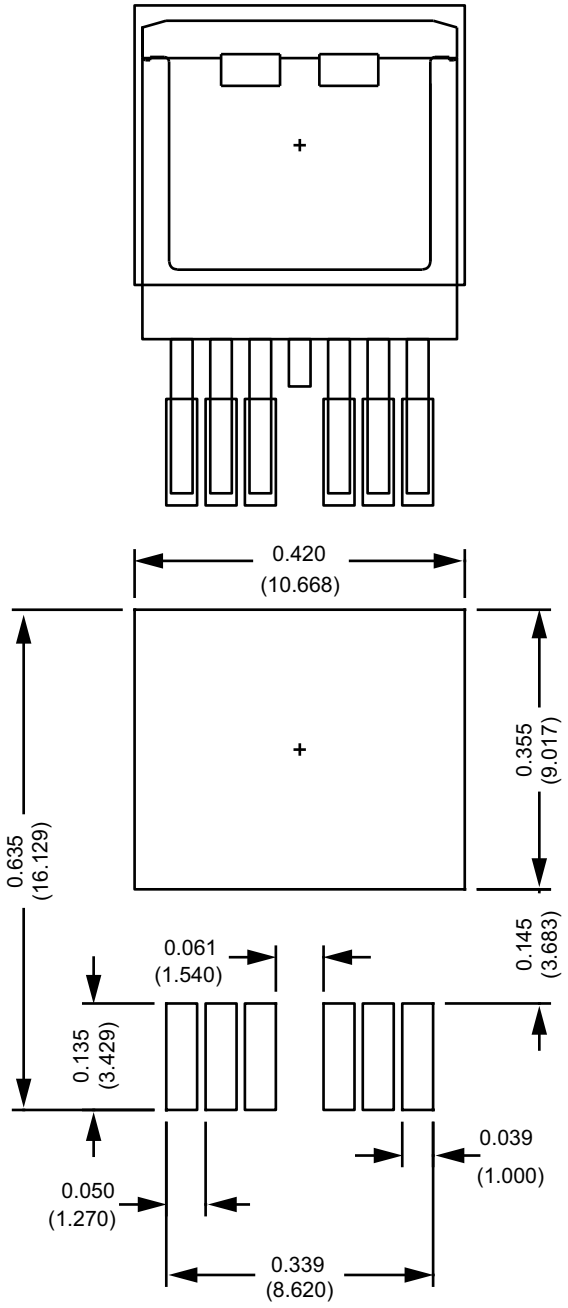


Notes

1. Plane B includes maximum features of heat sink tab and plastic
2. No more than 25 % of L1 can fall above seating plane by max. 8 mils
3. Pin to pin coplanarity max. 4 mils
4. Lead thickness 25 mils
5. For SUM part numbers lead thickness is 24 mils to 29 mils
6. For reference only
7. Use inches as the primary measurement
8. This feature is only for SUM

DIM.	INCHES		MILLIMETERS	
	MIN.	MAX.	MIN.	MAX.
A	0.160	0.190	4.064	4.826
b	0.020	0.039	0.508	0.990
b1	0.020	0.035	0.508	0.889
c* SUB	0.012	0.018	0.305	0.457
c* SUM	0.022	0.028	0.559	0.711
c1	0.018	0.025	0.457	0.635
c2	0.045	0.055	1.143	1.397
D	0.340	0.380	8.636	9.652
D1	0.260	0.280	6.604	7.112
D2	0.046	0.050	1.168	1.270
D3	0.045	0.055	1.143	1.397
E	0.380	0.410	9.652	10.414
E1	0.245	-	6.223	-
E2	0.072	0.078	1.829	1.981
e	0.050 BSC		1.27 BSC	
K	0.045	0.055	1.143	1.397
L	0.575	0.625	14.605	15.875
L1	0.090	0.110	2.286	2.794
L2	0.040	0.055	1.016	1.397
L3	0.050	0.070	1.270	1.778
L4	0.010 BSC		0.254 BSC	
M	-	0.002	-	0.050
ECN: T22-0410-Rev. D, 19-Sep-2022 DWG: 6006				

Recommended Land Pattern D²PAK (TO-263-7L)



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